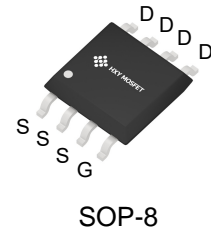




## Description

The NTMS4916NR2G uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



## General Features

$V_{DS} = 30V$   $I_D = 18A$

$R_{DS(ON)} < 6.5m\Omega$  @  $V_{GS}=10V$

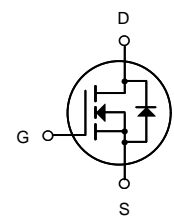
$R_{DS(ON)} < 12m\Omega$  @  $V_{GS}=4.5V$

## Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

## Package Marking and Ordering Information

| Product ID   | Pack  | Brand      | Qty(PCS) |
|--------------|-------|------------|----------|
| NTMS4916NR2G | SOP-8 | HXY MOSFET | 3000     |

## Absolute Maximum Ratings ( $T_c=25^\circ C$ unless otherwise noted)

| Symbol            | Parameter   | Limit      | Unit         |
|-------------------|---|------------|--------------|
| $V_{DS}$          | Drain-Source Voltage                                    | 30         | V            |
| $V_{GS}$          | Gate-Source Voltage                                     | $\pm 20$   | V            |
| $I_D$             | Drain Current-Continuous                                | 18         | A            |
| $I_D(70^\circ C)$ | Drain Current-Continuous( $T_c=70^\circ C$ )            | 8.2        | A            |
| $I_{DM}$          | Pulsed Drain Current                                    | 42         | A            |
| $P_D$             | Maximum Power Dissipation                               | 1.5        | W            |
| $T_J, T_{STG}$    | Operating Junction and Storage Temperature Range        | -55 To 150 | $^\circ C$   |
| $R_{\theta JC}$   | Thermal Resistance,Junction-to-Case <sup>(Note 2)</sup> | 36         | $^\circ C/W$ |



### Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

| Symbol                              | Parameter                                      | Conditions  | Min. | Typ.  | Max.  | Unit  |
|-------------------------------------|--|---|------|-------|-------|-------|
| BV <sub>DSS</sub>                   | Drain-Source Breakdown Voltage                 | V <sub>GS</sub> =0V, I <sub>D</sub> =250uA  | 30   | ---   | ---   | V     |
| ΔBV <sub>DSS</sub> /ΔT <sub>J</sub> | BVDSS Temperature Coefficient                  | Reference to 25°C, I <sub>D</sub> =1mA  | ---  | 0.027 | ---   | V/°C  |
| R <sub>DS(on)</sub>                 | Static Drain-Source On-Resistance <sup>2</sup> | V <sub>GS</sub> =10V, I <sub>D</sub> =10A   | ---  | 5.5   | 6.5   | mΩ    |
|                                     |  | V <sub>GS</sub> =4.5V, I <sub>D</sub> =8A   | ---  | 9     | 12    |       |
| V <sub>GS(th)</sub>                 | Gate Threshold Voltage                         | V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA                                | 1.2  | 1.5   | 2.5   | V     |
| ΔV <sub>GS(th)</sub>                | V <sub>GS(th)</sub> Temperature Coefficient    |   | ---  | -5.8  | ---   | mV/°C |
| I <sub>DSS</sub>                    | Drain-Source Leakage Current                   | V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C                         | ---  | ---   | 1     | uA    |
|                                     |  | V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C                         | ---  | ---   | 5     |       |
| I <sub>GSS</sub>                    | Gate-Source Leakage Current                    | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V  | ---  | ---   | ±100  | nA    |
| g <sub>fs</sub>                     | Forward Transconductance                       | V <sub>DS</sub> =5V, I <sub>D</sub> =10A  | ---  | 5.8   | ---   | S     |
| R <sub>g</sub>                      | Gate Resistance                                | V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz  | ---  | 2.2   | 3.8   | Ω     |
| Q <sub>g</sub>                      | Total Gate Charge (4.5V)                       | V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A                        | ---  | 12.6  | 17.6  | nC    |
| Q <sub>gs</sub>                     | Gate-Source Charge                             |   | ---  | 4.2   | 5.9   |       |
| Q <sub>gd</sub>                     | Gate-Drain Charge                              |   | ---  | 5.1   | 7.1   |       |
| T <sub>d(on)</sub>                  | Turn-On Delay Time                             | V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω<br>I <sub>D</sub> =10A | ---  | 6.2   | 12.4  | ns    |
| T <sub>r</sub>                      | Rise Time                                      |   | ---  | 59    | 106   |       |
| T <sub>d(off)</sub>                 | Turn-Off Delay Time                            |   | ---  | 27.6  | 55    |       |
| T <sub>f</sub>                      | Fall Time                                      |   | ---  | 8.4   | 16.8  |       |
| C <sub>iss</sub>                    | Input Capacitance                              | V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz                                       | ---  | 1317  | 1845  | pF    |
| C <sub>oss</sub>                    | Output Capacitance                             |   | ---  | 163   | 228.2 |       |
| C <sub>rss</sub>                    | Reverse Transfer Capacitance                   |   | ---  | 131   | 183.4 |       |
| I <sub>S</sub>                      | Continuous Source Current <sup>1,5</sup>       | V <sub>G</sub> =V <sub>D</sub> =0V, Force Current                                       | ---  | ---   | 18    | A     |
| I <sub>SM</sub>                     | Pulsed Source Current <sup>2,5</sup>           |   | ---  | ---   | 42    | A     |
| V <sub>SD</sub>                     | Diode Forward Voltage <sup>2</sup>             | V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C                           | ---  | ---   | 1.2   | V     |
| t <sub>rr</sub>                     | Reverse Recovery Time                          | I <sub>F</sub> =10A, dI/dt=100A/μs, T <sub>J</sub> =25°C                                | ---  | 12.5  | ---   | nS    |
| Q <sub>rr</sub>                     | Reverse Recovery Charge                        |   | ---  | 5     | ---   | nC    |

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V,V<sub>GS</sub>=10V,L=0.1mH,I<sub>AS</sub>=35A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.



## Typical Characteristics

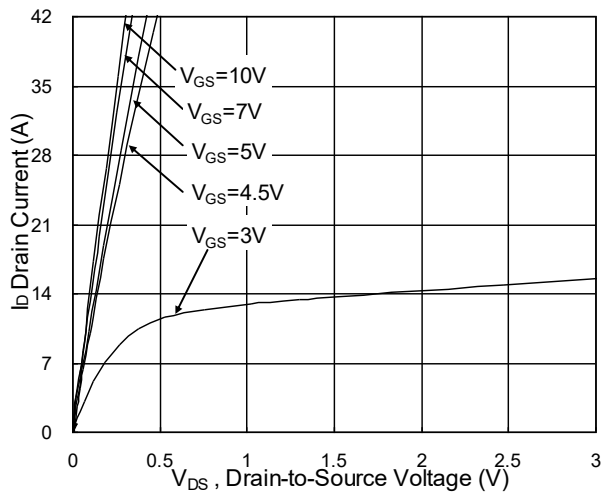


Fig.1 Typical Output Characteristics

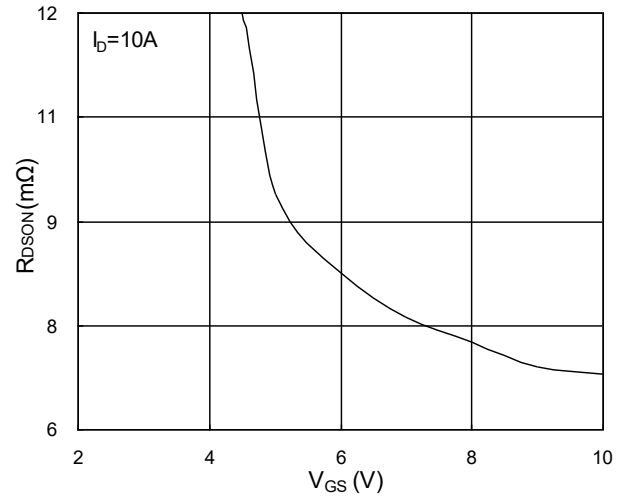


Fig.2 On-Resistance vs. Gate-Source

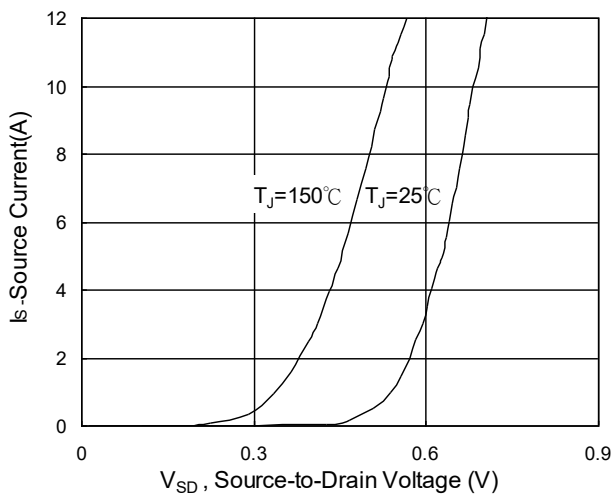


Fig.3 Forward Characteristics of reverse

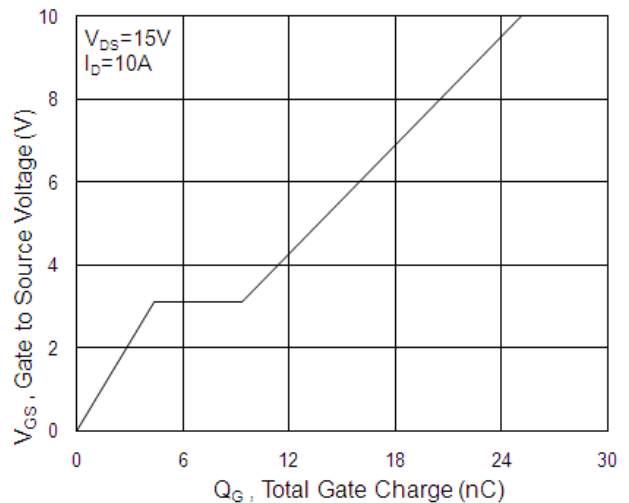


Fig.4 Gate-Charge Characteristics

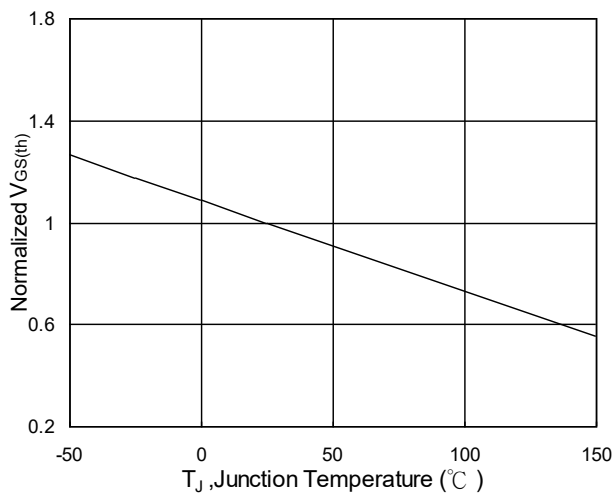


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

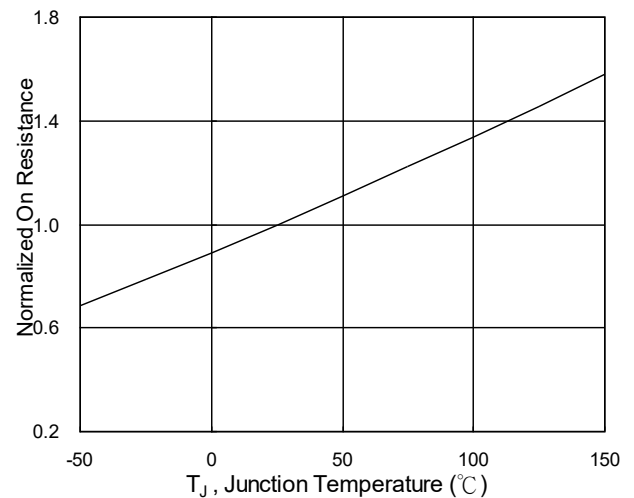


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

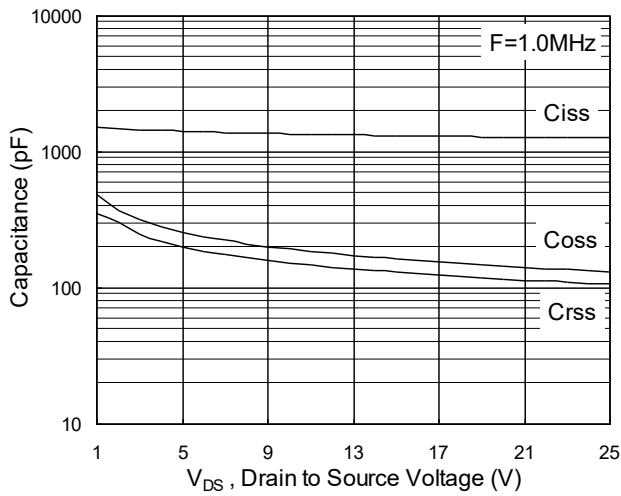


Fig.7 Capacitance

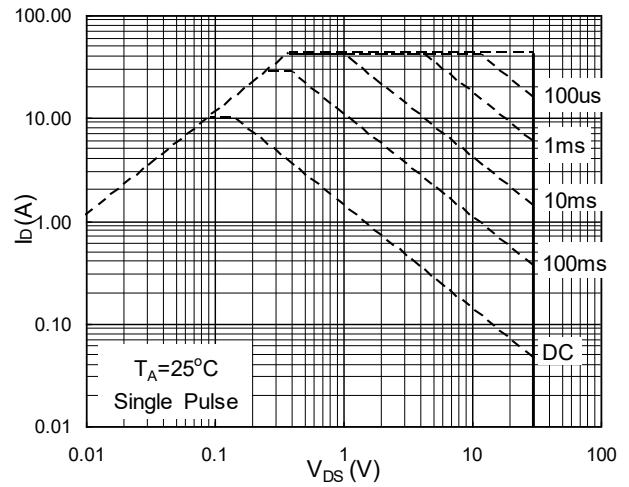


Fig.8 Safe Operating Area

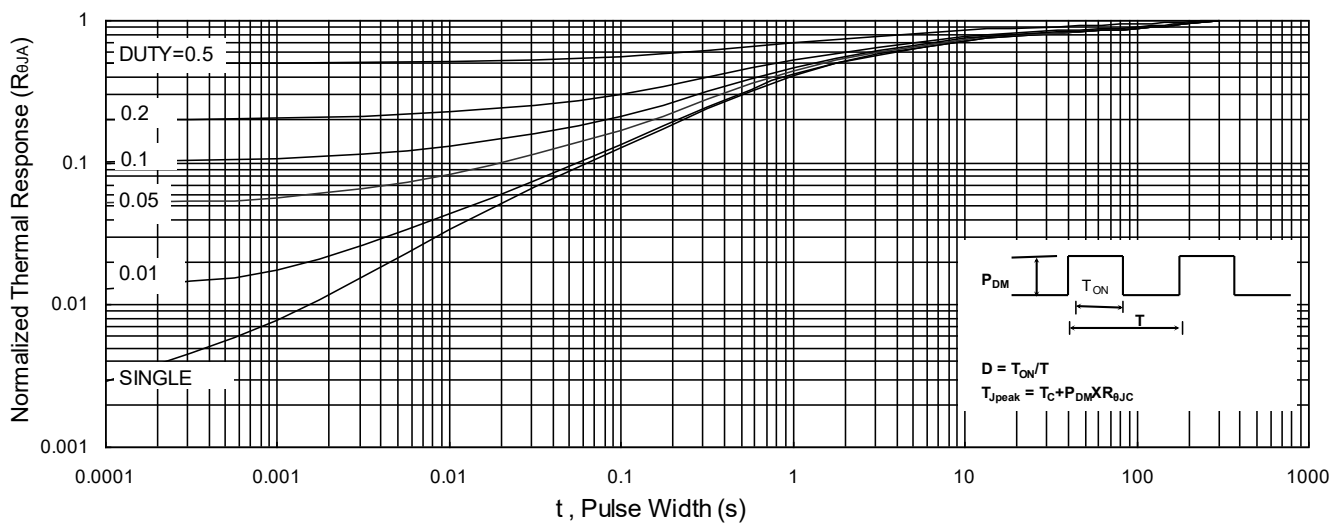


Fig.9 Normalized Maximum Transient Thermal Impedance

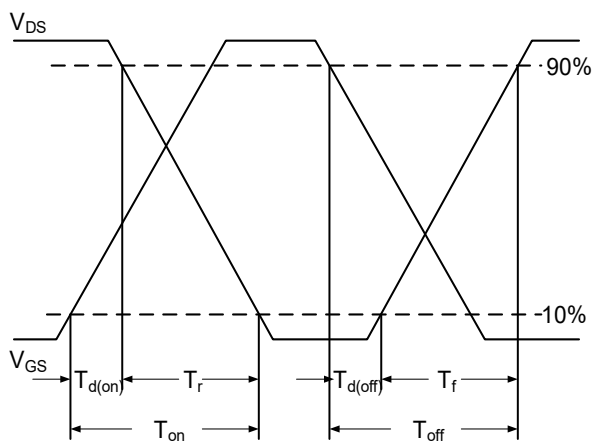


Fig.10 Switching Time Waveform

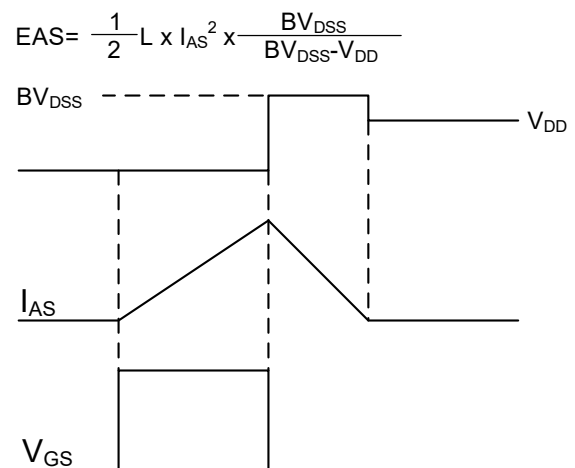
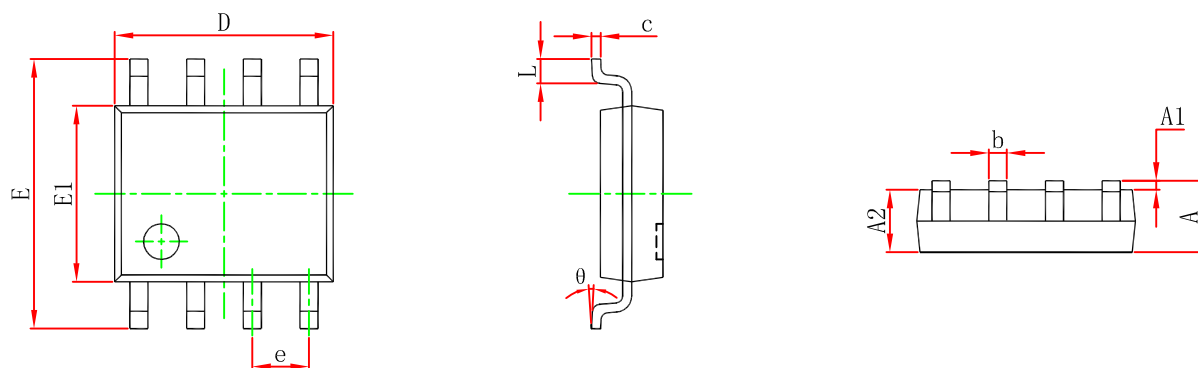


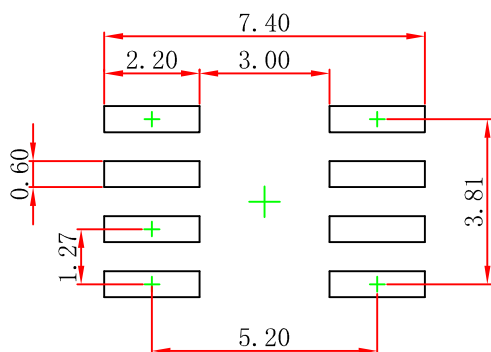
Fig.11 Unclamped Inductive Switching Waveform



## SOP-8 Package Outline Dimensions



| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | Min                       | Max   | Min                  | Max   |
| A      | 1.350                     | 1.750 | 0.053                | 0.069 |
| A1     | 0.100                     | 0.250 | 0.004                | 0.010 |
| A2     | 1.350                     | 1.550 | 0.053                | 0.061 |
| b      | 0.330                     | 0.510 | 0.013                | 0.020 |
| c      | 0.170                     | 0.250 | 0.007                | 0.010 |
| D      | 4.800                     | 5.000 | 0.189                | 0.197 |
| e      | 1.270 (BSC)               |       | 0.050 (BSC)          |       |
| E      | 5.800                     | 6.200 | 0.228                | 0.244 |
| E1     | 3.800                     | 4.000 | 0.150                | 0.157 |
| L      | 0.400                     | 1.270 | 0.016                | 0.050 |
| θ      | 0°                        | 8°    | 0°                   | 8°    |



Note:  
1. Controlling dimension; in millimeters.  
2. General tolerance:  $\pm 0.05\text{mm}$ .  
3. The pad layout is for reference purposes only.



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